

<b>Notice of References Cited</b>		Application/Control No.	Applicant(s)/Patent Under Reexamination	
		10/643,944	HASEGAWA ET AL.	
Examiner <i>Tod T. Van Roy</i>		Art Unit	2828	Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-6,580,736	06-2003	Yoshie et al.	372/45
	C	US-			
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	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

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	N	JP 11251687 A	09-1999	Japan	HASEGAWA et al.	H01S 03/18
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**NON-PATENT DOCUMENTS**

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	U	TOJYO, Tsuyoshi., et al. "GaN based High Power Blue Violet Laser Diodes." The Japan Society for Applied Physics, Volume 40. Pad 1. No. 5A, May 2001, pp.3206-3210
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.